

# **Excellent Integrated System Limited**

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Advanced Photonix, Inc. PDI-C109-F

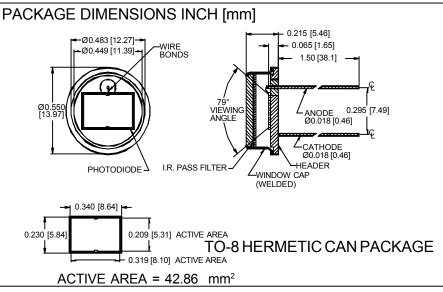
For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



Distributor of Advanced Photonix, Inc. : Excellent Integrated System Limited Datasheet of PDI-C109-F - PHOTODIODE IR 42.86MM SQ TO-8 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

# **PHOTONIC** DETECTORS INC.

# Silicon Photodiode, Near I.R. Photoconductive Type PDI-C109-F



## **FEATURES**

- High speed
- •
- Match to I.R. emitters .
- Hermetic package

## DESCRIPTION

The PDI-C109-F is a silicon, PIN planar I.R. pass visible rejection diffused photodiode with NIR pass, visible light rejection optical filter. Ideal for high speed, low capacitance, photoconductive NIR applications. Packaged in a hermetic TO-8 metal can with a flat window cap.

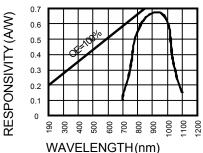
#### **APPLICATIONS**

- I.R. detector
- I.R. laser detector
- Photo-interrupters
- Industrial controls

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS			
Vbr	Reverse Voltage		100	V			
T <sub>STG</sub>	Storage Temperature	-55	+100	°C			
То	Operating Temperature Range	-40	+80	ъ			
Ts	Soldering Temperature*		+240	с			
Ι	Light Current		500	mA			

### SPECTRALRESPONSE



\*1/16 inch from case for 3 secs max

#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS				
lsc	Short Circuit Current	H = 100 fc, 2850 K	405	450		$\mu$ A				
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		5	15	nA				
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	30	100		MΩ				
TC RSH	RSH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		%/℃				
C	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		120		pF				
λrange	Spectral Application Range	Spot Scan	700		1100	nm				
λρ	Spectral Response - Peak	Spot Scan		950		nm				
Vbr	Breakdown Voltage	I = 10 μA	30	50		V				
NEP	Noise Equivalent Power	VR = 10 V @ Peak		5x10 <sup>-13</sup>		W/√ <sup>Hz</sup>				
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 50 V		25		nS				

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f=1 MHz [FORM NO. 100-PDI-C109-F REV A]